



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-323 Plastic-Encapsulate DIODE

BAS40W SERIES SCHOTTKY DIODE

FEATURES

Power dissipation

P_D : 200 mW ($T_{amb}=25$)

Collector current

I_F : 200 mA

Collector-base voltage

V_R : 40V

Operating and storage junction temperature range

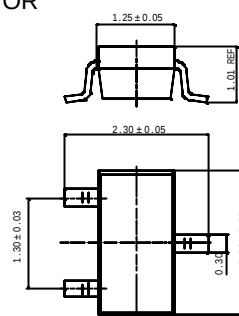
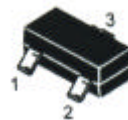
T_J , T_{stg} : -55 to +150

SOT-323

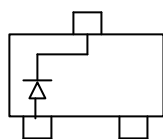
1.BASE

2.EMITTER

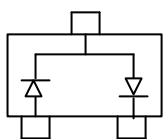
3.COLLECTOR



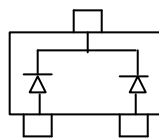
Unit : mm



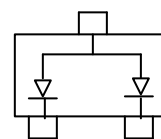
BAS40W Marking:43.K43



BAS40W-04 Marking:44.K44



BAS40W-05 Marking:45.K45



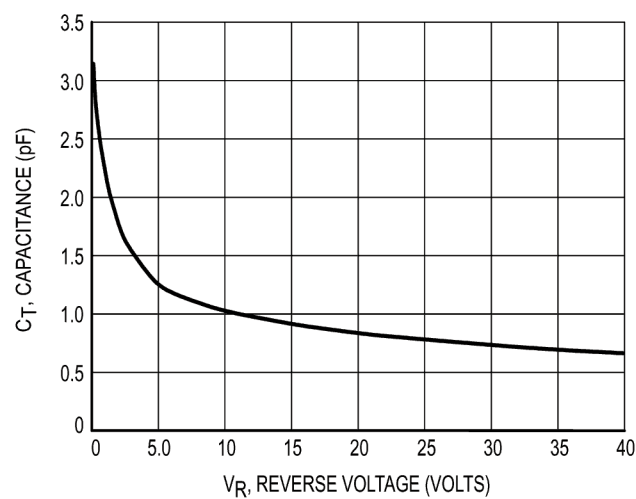
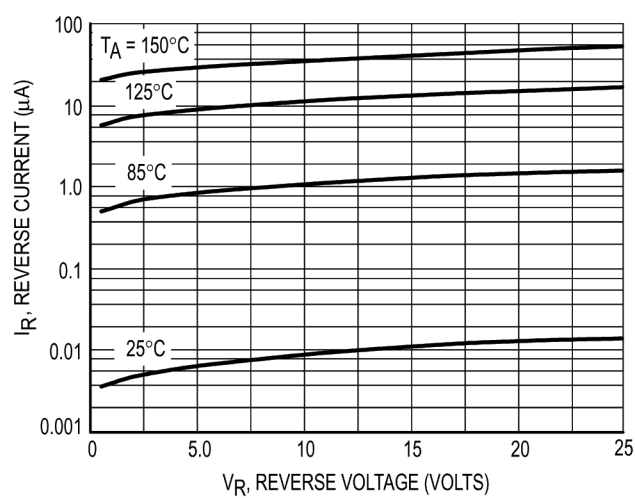
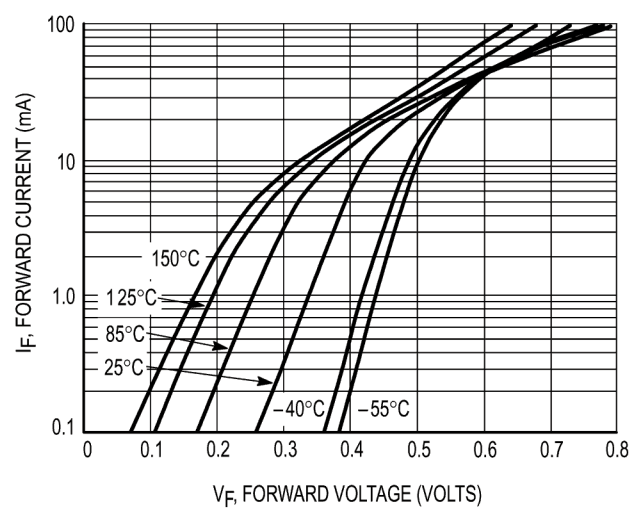
BAS40W-06 Marking:46.K46

ELECTRICAL CHARACTERISTICS ($T_{amb}=25$ unless otherwise specified)

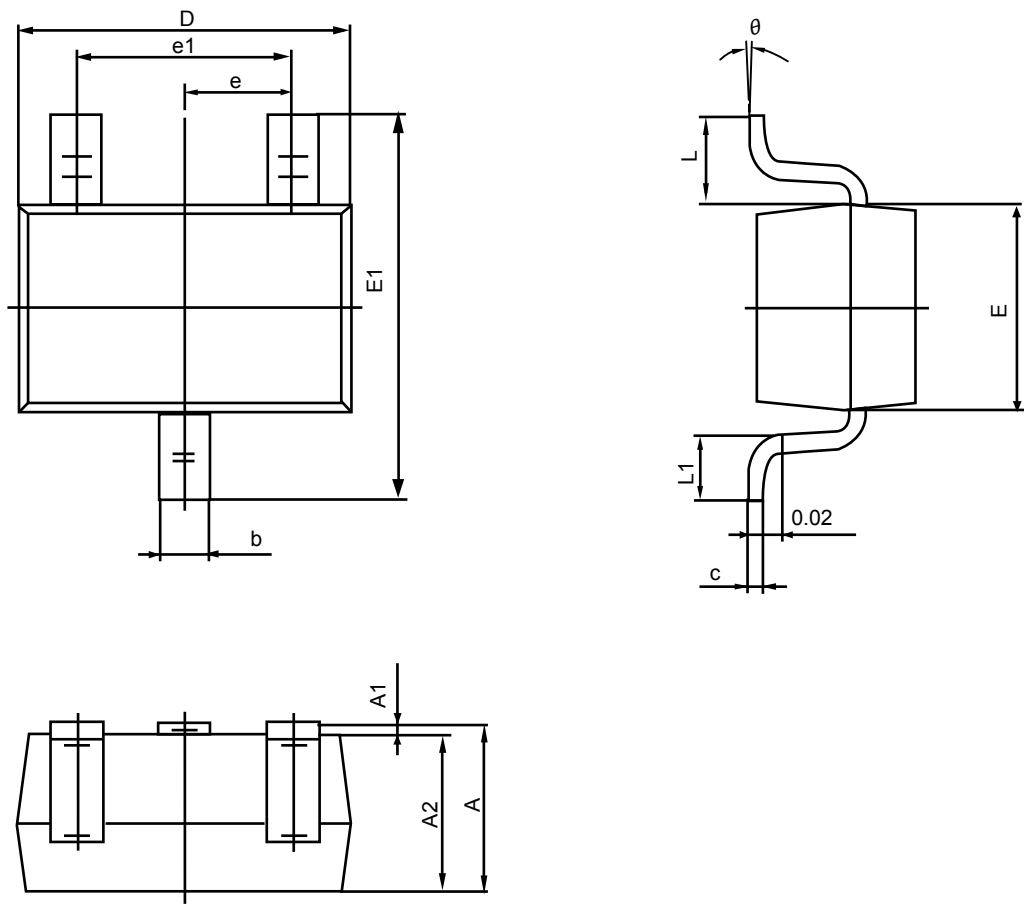
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R = 10\mu A$	40		V
Reverse voltage leakage current	I_R	$V_R = 30V$		200	nA
Forward voltage	V_F	$I_F = 1mA$ $I_F = 40mA$		380 1000	mV
Diode capacitance	C_D	$V_R = 0V$ $f = 1MHz$		5	pF
Reveres recovery time	t_{rr}	$I_F = 10mA$ through $I_R = 10mA$ to $I_R = 1mA$		5	nS

Typical Characteristics

BAS40W



SOT-323 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°